

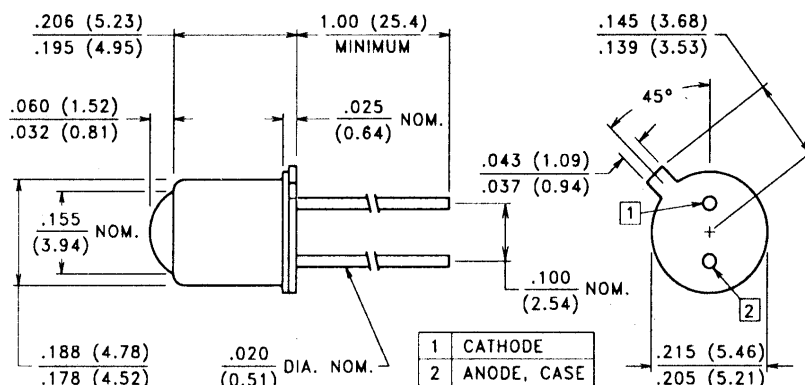
GaAlAs Infrared Emitting Diodes

TO-46 Lensed Package — 880 nm

VTE1163



PACKAGE DIMENSIONS inch (mm)



CASE 24 TO-46 HERMETIC (Lensed)

CHIP SIZE: .018" x .018"

DESCRIPTION

This narrow beam angle TO-46 hermetic emitter contains a large area, double wirebonded, GaAlAs, 880 nm, high efficiency IRED chip suitable for higher current pulse applications.

ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted) ■

Maximum Temperatures			
Storage and Operating:	-55°C to 125°C	Maximum Reverse Voltage:	5.0V
Continuous Power Dissipation:	200 mW	Maximum Reverse Current @ $V_R = 5V$:	10 μA
Derate above 30°C:	2.11 mW/°C	Peak Wavelength (Typical):	880 nm
Maximum Continuous Current:	100 mA	Junction Capacitance @ 0V, 1 MHz (Typ.):	35 pF
Derate above 30°C:	1.05 mA/°C	Response Time @ $I_F = 20$ mA	
Peak Forward Current, 10 μs , 100 pps:	3A	Rise: 1.0 μs Fall: 1.0 μs	
Temp. Coefficient of Power Output (Typ.):	-.8%/°C	Lead Soldering Temperature:	260°C
		(1.6 mm from case, 5 seconds max.)	

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also GaAlAs curves, pages 108-110)

Part Number ■	Output							Forward Drop		Half Power Beam Angle
	Irradiance				Radiant Intensity	Total Power	Test Current	V _F		
	E _e		Condition		I _e	P _O	I _{FT}	@ I _{FT}		θ _{1/2}
	mW/cm ²		distance	Diameter	mW/sr	mW	mA (Pulsed)	Volts		Typ.
	Min.	Typ.	mm	mm	Min.	Typ.		Typ.	Max.	
VTE1163	22	28	36	6.4	285	110	1.0	2.8	3.5	±10°

■ Refer to General Product Notes, page 2.